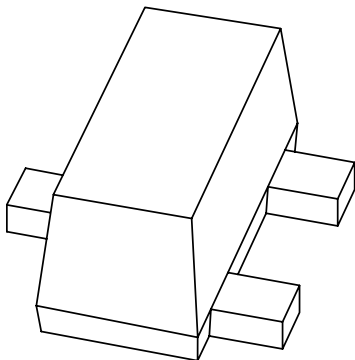


# DATA SHEET



**PBSS2515F**

15 V low  $V_{CEsat}$  NPN transistor

Product specification  
Supersedes data of 2001 Jan 26

2001 Sep 21

# 15 V low $V_{CEsat}$ NPN transistor

# PBSS2515F

## FEATURES

- Low collector-emitter saturation voltage
- High current capabilities
- Improved thermal behaviour due to flat leads.

## APPLICATIONS

- General purpose switching and muting
- Low frequency driver circuits
- LCD backlighting
- Audio frequency general purpose amplifier applications
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

## DESCRIPTION

NPN low  $V_{CEsat}$  transistor in a SC-89 (SOT490) plastic package.  
 PNP complement: PBSS3515F.

## MARKING

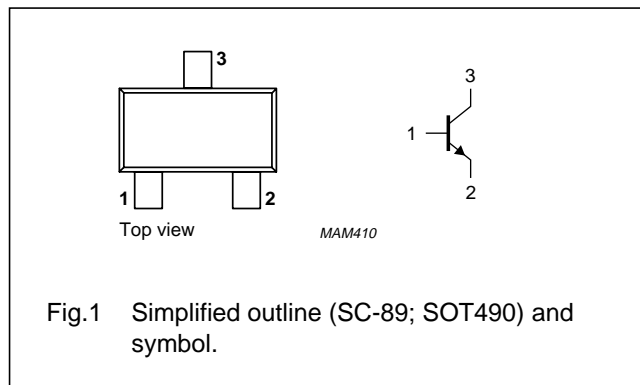
TYPE NUMBER	MARKING CODE
PBSS2515F	2A

## QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	15	V
$I_C$	collector current (DC)	500	mA
$I_{CM}$	peak collector current	1	A
$R_{CEsat}$	equivalent on-resistance	<500	m $\Omega$

## PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	15	V
$V_{CEO}$	collector-emitter voltage	open base	–	15	V
$V_{EBO}$	emitter-base voltage	open collector	–	6	V
$I_C$	collector current (DC)		–	500	mA
$I_{CM}$	peak collector current		–	1	A
$I_{BM}$	peak base current		–	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	250	mW
$T_{stg}$	storage temperature		–65	+150	$^\circ\text{C}$
$T_j$	junction temperature		–	150	$^\circ\text{C}$
$T_{amb}$	operating ambient temperature		–65	+150	$^\circ\text{C}$

15 V low  $V_{CEsat}$  NPN transistor

## PBSS2515F

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air	500	K/W

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ ; unless otherwise specified.

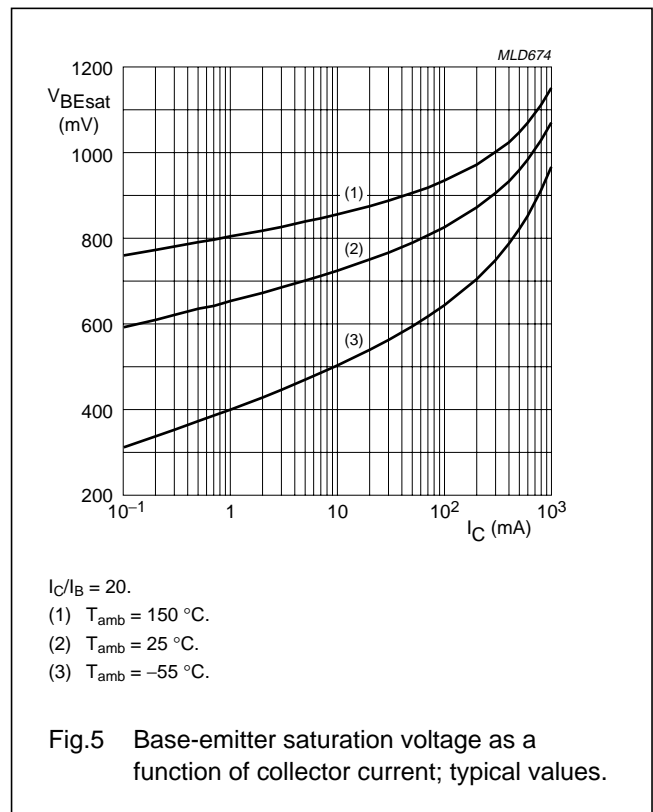
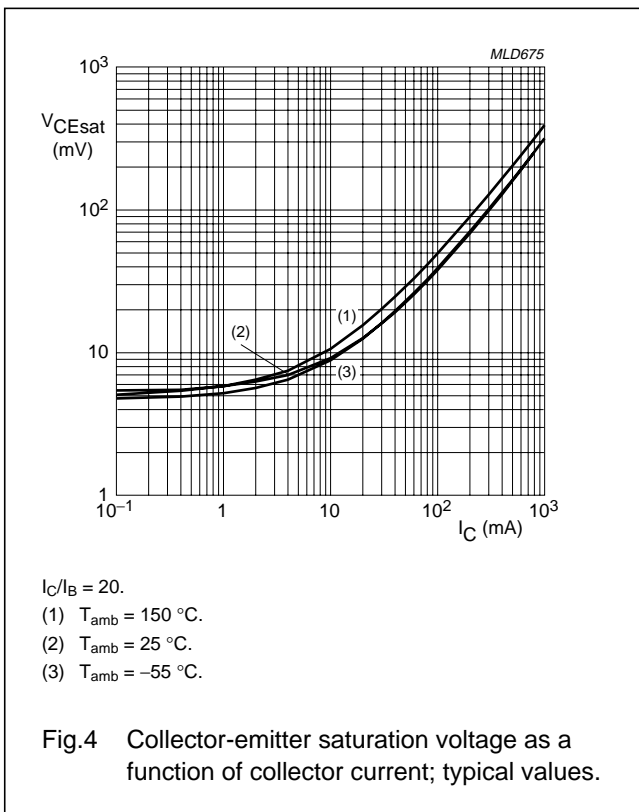
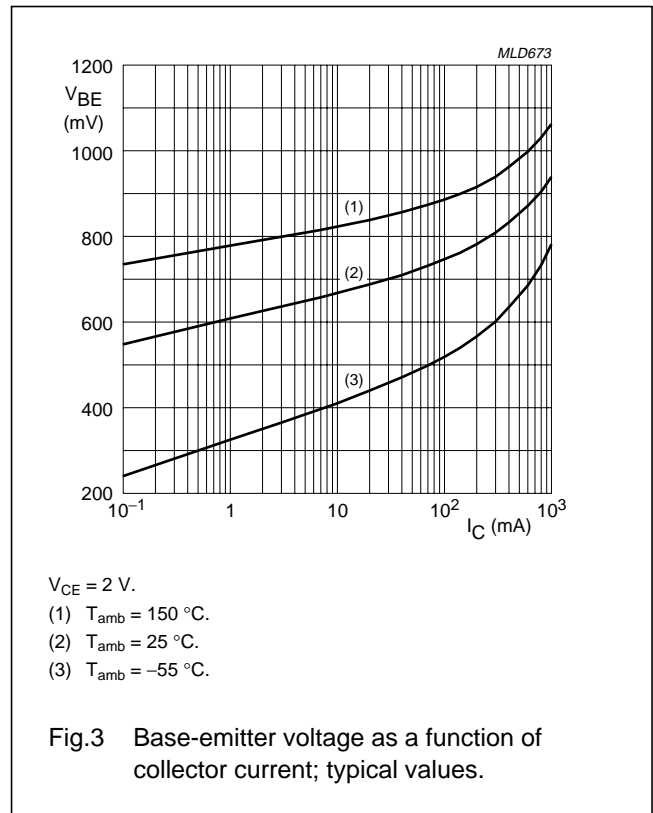
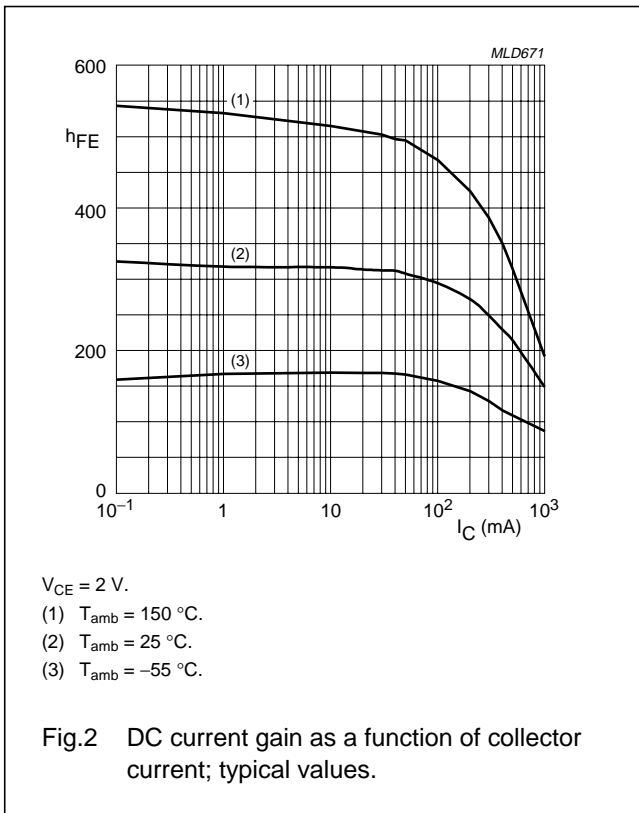
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 15\text{ V}; I_E = 0$	–	–	100	nA
		$V_{CB} = 15\text{ V}; I_E = 0; T_J = 150\text{ °C}$	–	–	50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0$	–	–	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 2\text{ V}; I_C = 10\text{ mA}$	200	–	–	
		$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}; \text{note 1}$	150	–	–	
		$V_{CE} = 2\text{ V}; I_C = 500\text{ mA}; \text{note 1}$	90	–	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	–	25	mV
		$I_C = 200\text{ mA}; I_B = 10\text{ mA}$	–	–	150	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	–	250	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	300	<500	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	–	1.1	V
$V_{BE}$	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}; \text{note 1}$	–	–	0.9	V
$f_T$	transition frequency	$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	250	420	–	MHz
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	4.4	6	pF

## Note

1. Pulse test:  $t_p \leq 300\ \mu\text{s}$ ;  $\delta \leq 0.02$ .

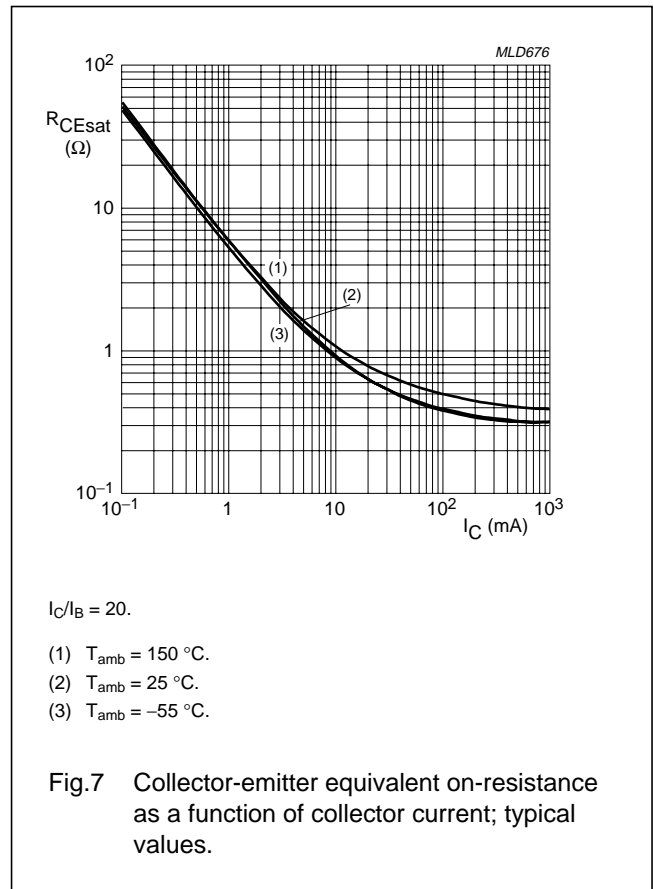
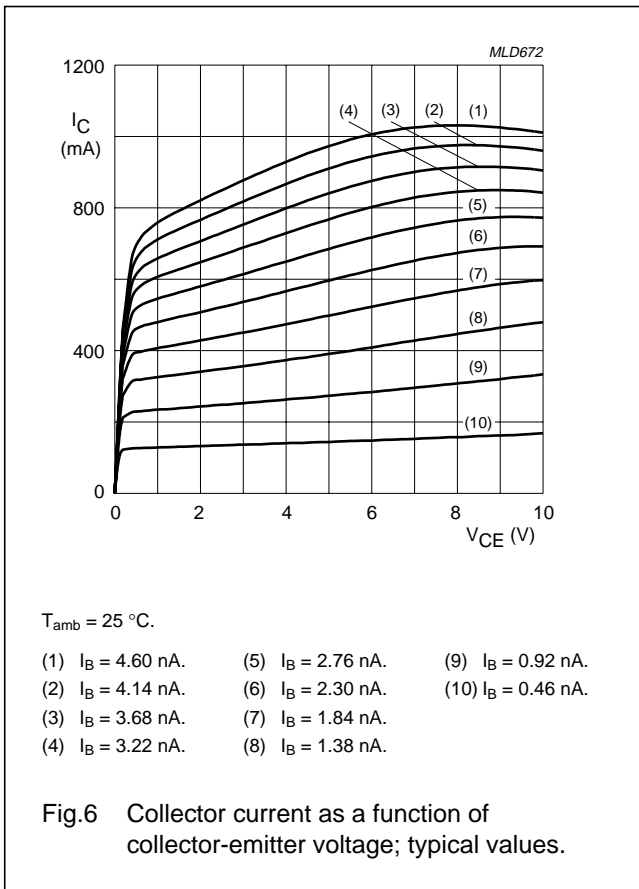
15 V low  $V_{CEsat}$  NPN transistor

PBSS2515F



15 V low  $V_{CEsat}$  NPN transistor

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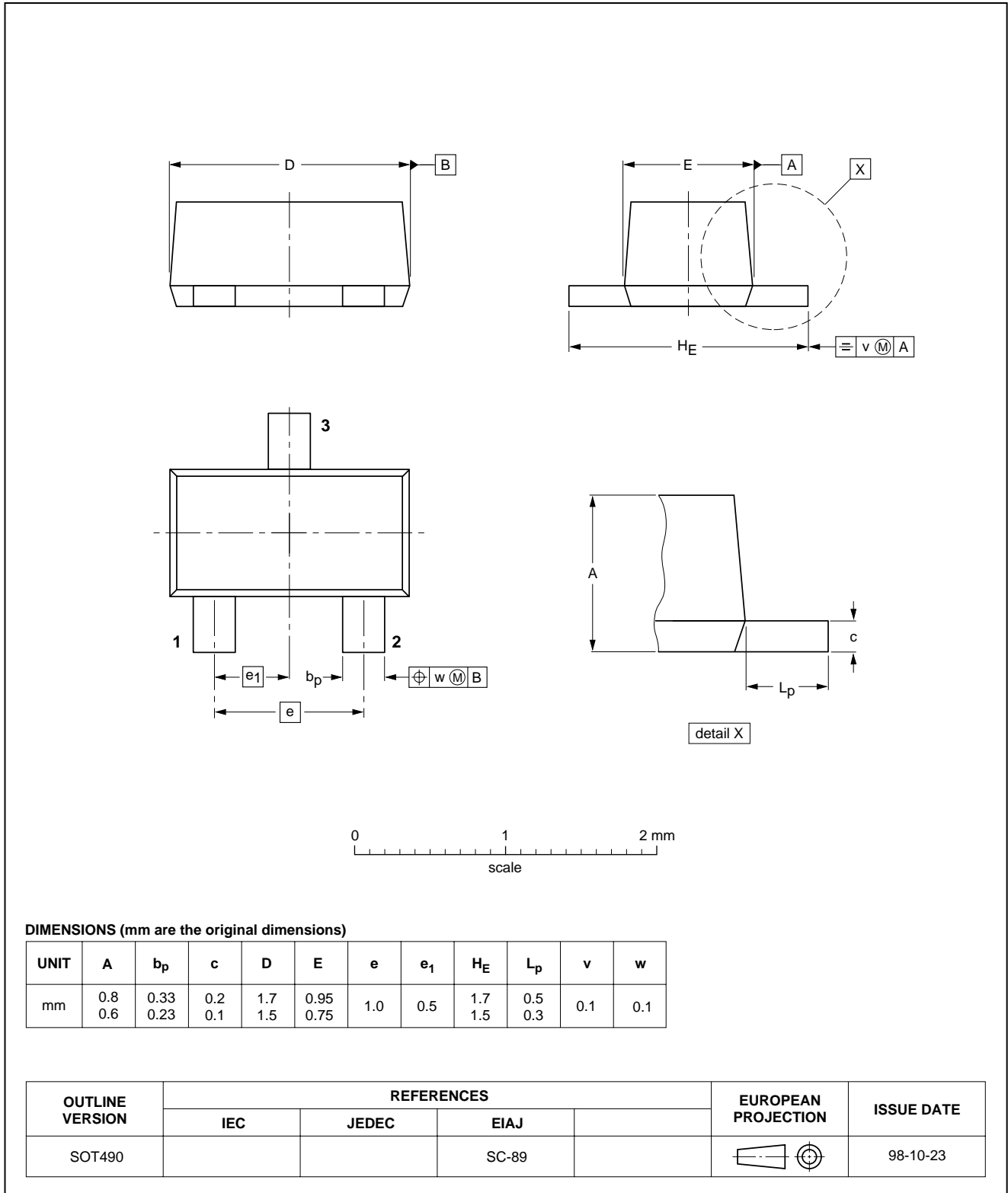
15 V low  $V_{CEsat}$  NPN transistor

PBSS2515F

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT490



15 V low  $V_{CEsat}$  NPN transistor

PBSS2515F

## DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
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